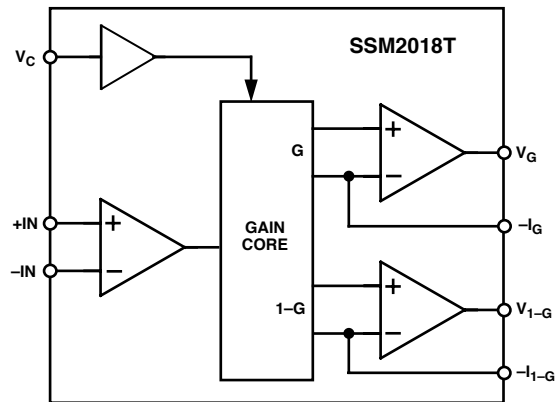


### FEATURES

- 117 dB Dynamic Range
- 0.006% Typical THD+N (@ 1 kHz, Unity Gain)
- 140 dB Gain Range
- No External Trimming Required
- Differential Inputs
- Complementary Gain Outputs
- Buffered Control Port
- I-V Converter On-Chip
- Low External Parts Count
- Low Cost

### FUNCTIONAL BLOCK DIAGRAM



### GENERAL DESCRIPTION

The SSM2018T represents continuing evolution of the Frey Operational Voltage Controlled Element (OVCE) topology that permits flexibility in the design of high performance volume control systems. The SSM2018T is laser trimmed for gain core symmetry and offset. As a result, the SSM2018T is the first professional audio quality VCA to offer trimless operation.

Due to careful gain core layout, the SSM2018T combines the low noise of Class AB topologies with the low distortion of Class A circuits to offer an unprecedented level of sonic trans-

parency. Additional features include differential inputs, a 140 dB (–100 dB to +40 dB) gain range and a high impedance control port. The SSM2018T provides an internal current-to-voltage converter. Thus no external active components are required.

This device is offered in 16-lead plastic DIP and SOIC packages and guaranteed for operation over the extended industrial temperature range of –40°C to +85°C.

**NEW E GRADE  
0.01% THD+N MAX**

\*Protected by U.S. Patent Nos. 4,471,320 and 4,560,947.

### REV. B

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# SSM2018T—SPECIFICATIONS

**ELECTRICAL SPECIFICATIONS** ( $V_S = \pm 15\text{ V}$ ,  $A_V = 0\text{ dB}$ ,  $R_L = 100\text{ k}\Omega$ ,  $f = 1\text{ kHz}$ ,  $0\text{ dBu} = 0.775\text{ V rms}$ , simple VCA application circuit with  $18\text{ k}\Omega$  resistors,  $-V_{IN}$  floating, and Class AB gain core bias ( $R_B = 150\text{ k}\Omega$ ),  $-40^\circ\text{C} < T_A < +85^\circ\text{C}$ , unless otherwise noted. Typical specifications apply at  $T_A = 25^\circ\text{C}$ .)

Parameter	Conditions	Min	Typ	Max	Max (E Grade)	Unit
<b>AUDIO PERFORMANCE</b>						
Noise	$V_{IN} = \text{GND}$ , 20 kHz Bandwidth		-95	-93		dBu
Headroom	Clip Point = 1% THD + N		22			dBu
Total Harmonic Distortion plus Noise	2nd and 3rd Harmonics Only ( $25^\circ\text{C}$ to $85^\circ\text{C}$ )					
	$A_V = 0\text{ dB}$ , $V_{IN} = +10\text{ dBu}$		0.006	0.020	0.01	%
	$A_V = +20\text{ dB}$ , $V_{IN} = -10\text{ dBu}$		0.013	0.03	0.02	%
	$A_V = -20\text{ dB}$ , $V_{IN} = +10\text{ dBu}$		0.013	0.03	0.02	%
<b>INPUT AMPLIFIER</b>						
Bias Current	$V_{CM} = 0\text{ V}$		0.25	1		$\mu\text{A}$
Offset Voltage	$V_{CM} = 0\text{ V}$		1	15		mV
Offset Current	$V_{CM} = 0\text{ V}$		10	100		nA
Input Impedance			4			$\text{M}\Omega$
Common-Mode Range			$\pm 13$			V
Gain Bandwidth	VCA Configuration		0.7			MHz
	VCP Configuration		14			MHz
Slew Rate			5			$\text{V}/\mu\text{s}$
<b>OUTPUT AMPLIFIER</b>						
Offset Voltage	$V_{IN} = 0\text{ V}$ , $V_C = 4\text{ V}$		1.0	15		mV
Output Voltage Swing	$I_{OUT} = 1.5\text{ mA}$					
	Positive	10	13			V
	Negative	-10	-14			V
Minimum Load Resistance	For Full Output Swing		9			$\text{k}\Omega$
<b>CONTROL PORT</b>						
Bias Current			0.36	1		$\mu\text{A}$
Input Impedance			1			$\text{M}\Omega$
Gain Constant	Device Powered in Socket > 60 sec		-30			mV/dB
Gain Constant Temperature Coefficient			-3500			ppm/ $^\circ\text{C}$
Control Feedthrough	0 dB to -40 dB Gain Range		$\pm 1$	$\pm 4$	$\pm 3$	mV
Maximum Gain	$V_C = -1.3\text{ V}$		40			mV
Maximum Attenuation	$V_C = 4\text{ V}$		100			dB
<b>POWER SUPPLIES</b>						
Supply Voltage Range		$\pm 5$		$\pm 18$		V
Supply Current			11	15		mA
Power Supply Rejection Ratio			80			dB

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

Supply Voltage	
Dual Supply	.....±18 V
Input Voltage	..... ±V <sub>S</sub>
Operating Temperature Range	.....-40°C to +85°C
Storage Temperature	.....-65°C to +150°C
Junction Temperature (T <sub>J</sub> )	..... 150°C
Lead Temperature (Soldering, 60 sec)	..... 300°C

## THERMAL CHARACTERISTICS

Thermal Resistance <sup>2</sup>	
16-Lead Plastic DIP	
θ <sub>JA</sub>	..... 76°C/W
θ <sub>JC</sub>	..... 33°C/W
16-Lead SOIC	
θ <sub>JA</sub>	..... 92°C/W
θ <sub>JC</sub>	..... 27°C/W

## TRANSISTOR COUNT

Number of Transistors	
SSM2018T	..... 125

## ESD RATINGS

883 (Human Body) Model	..... 500 V
EIAJ Model	..... 100 V

## NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>2</sup>θ<sub>JA</sub> is specified for worst-case conditions, i.e.; θ<sub>JA</sub> is specified for device in socket for P-DIP and device soldered in circuit board for SOIC package.

## ORDERING GUIDE

Model	Temperature Range	Package Option <sup>1</sup>
SSM2018TP	-40°C to +85°C	N-16
SSM2018TS <sup>2</sup>	-40°C to +85°C	R-16

<sup>1</sup>N = Plastic DIP; R = SOL.

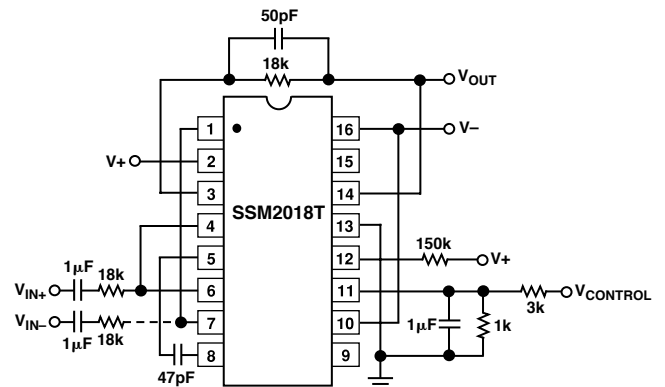
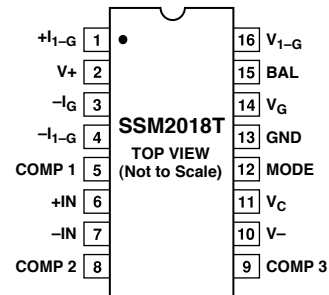
<sup>2</sup>Not for new designs; obsolete April 2002.

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the SSM2018T features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

## PIN CONFIGURATION

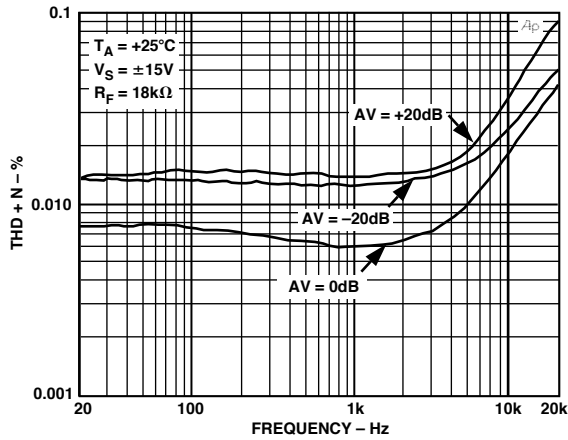
### 16-Lead Plastic DIP and SOL



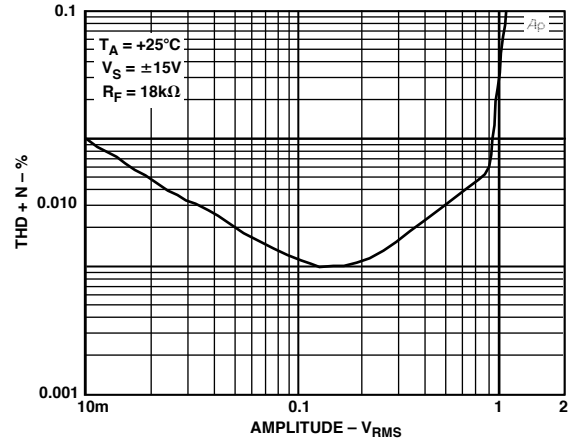
SSM2018T Typical Application Circuit



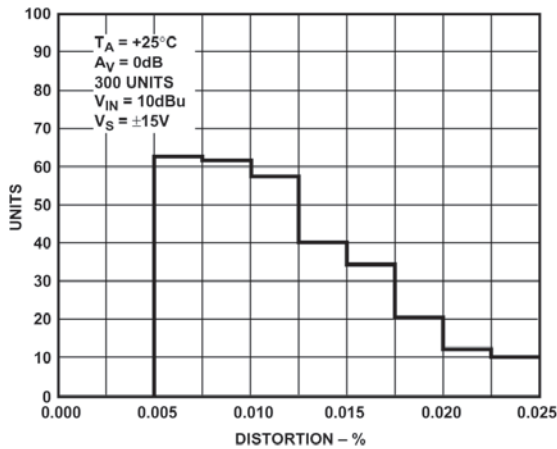
# SSM2018T—Typical Performance Characteristics



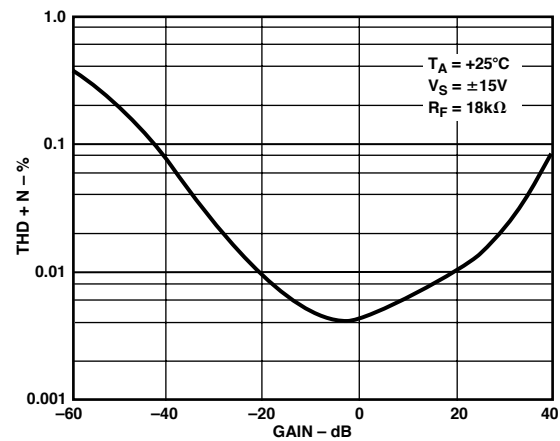
TPC 1. SSM2018T THD + N Frequency (80 kHz Low-Pass Filter, for  $A_V = 0$  dB,  $V_{IN} = 3$  V rms; for  $A_V = +20$  dB,  $V_{IN} = 0.3$  V rms; for  $A_V = -20$  dB,  $V_{IN} = 3$  V rms)



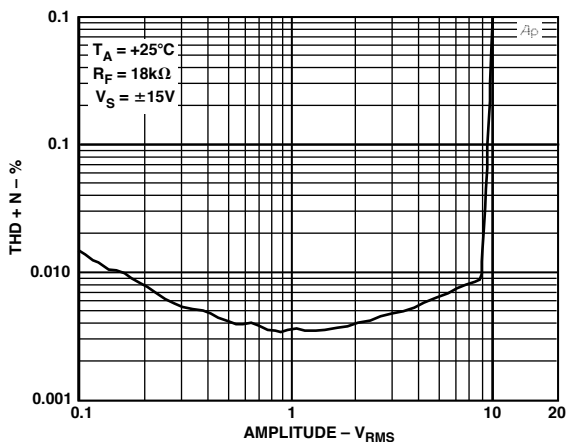
TPC 4. SSM2018T THD + N vs. Amplitude (Gain = +20 dB,  $f_{IN} = 1$  kHz, 80 kHz Low-Pass Filter)



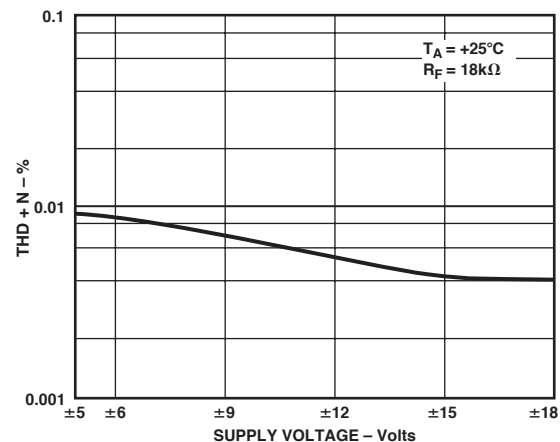
TPC 2. SSM2018T Distortion Distribution



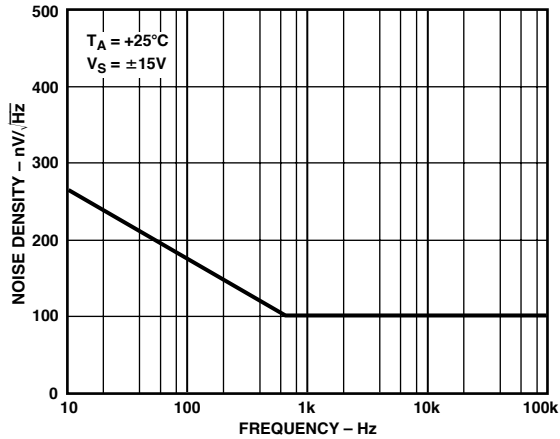
TPC 5. SSM2018T THD + N vs. Gain ( $f_{IN} = 1$  kHz; for  $-60$  dB  $\leq A_V \leq -20$  dB,  $V_{IN} = 10$  V rms; for  $0$  dB  $\leq A_V \leq +20$  dB,  $V_{IN} = 1$  V rms)



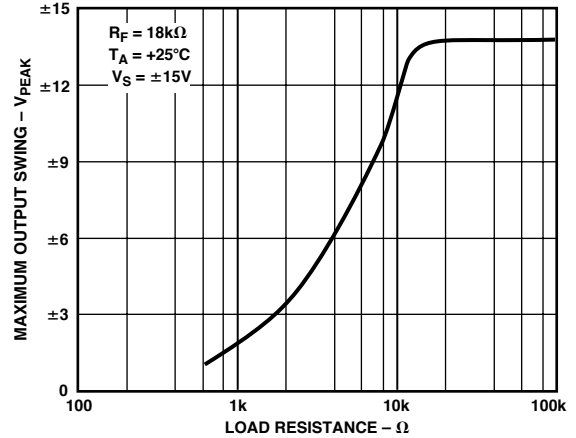
TPC 3. SSM2018T THD + N vs. Amplitude (Gain = 0 dB,  $f_{IN} = 1$  kHz, 80 kHz Low-Pass Filter)



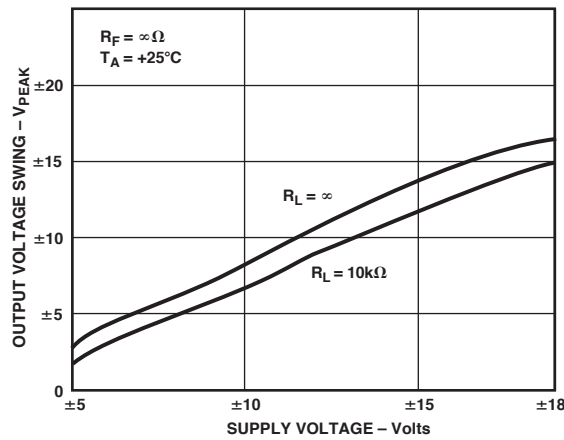
TPC 6. SSM2018T THD + N vs. Supply Voltage ( $A_V = 0$  dB,  $V_{IN} = 1$  V rms,  $f_{IN} = 1$  kHz, 80 kHz Low-Pass Filter)



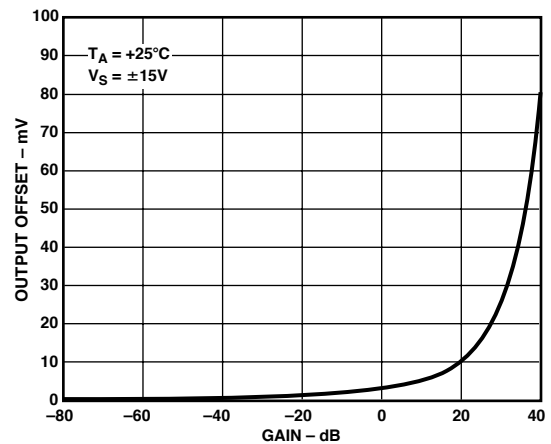
TPC 7. SSM2018T Noise Density vs. Frequency (Unity Gain, Referred to Input)



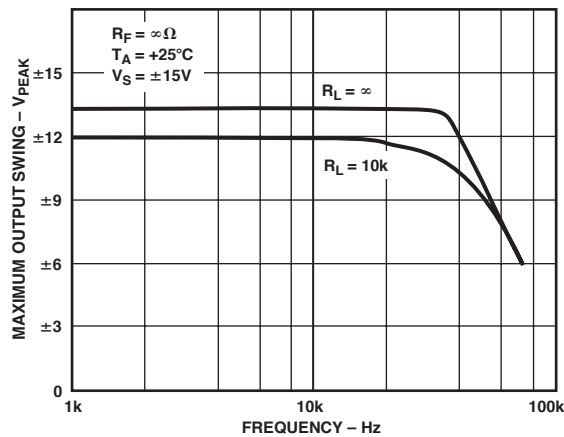
TPC 10. SSM2018T Maximum Output Swing vs. Load Resistance (THD = 1 % max)



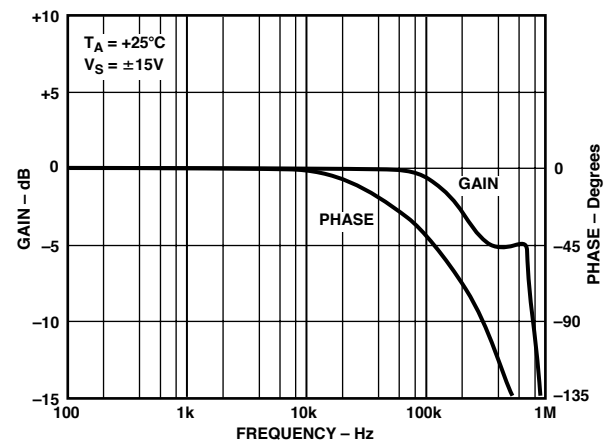
TPC 8. SSM2018T Maximum Output Swing vs. Supply Voltage (THD = 1% max)



TPC 11. SSM2018T Typical Output Offset vs. Gain

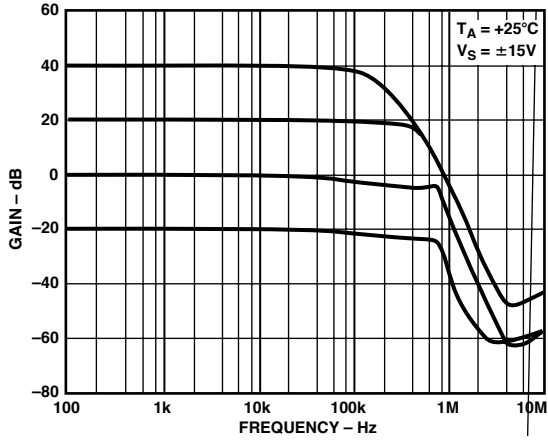


TPC 9. SSM2018T Maximum Output Swing vs. Frequency (THD = 1 % max)

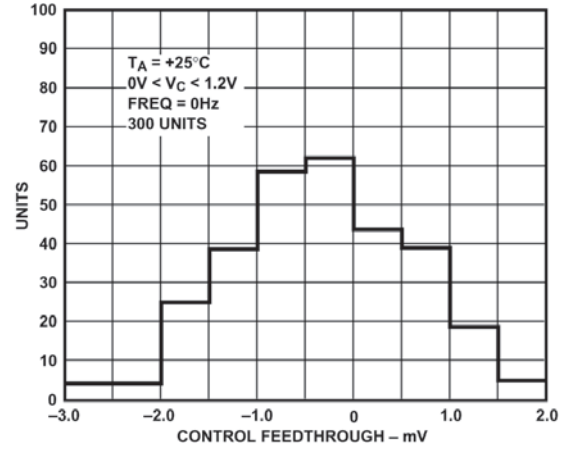


TPC 12. SSM2018T Gain/Phase vs. Frequency

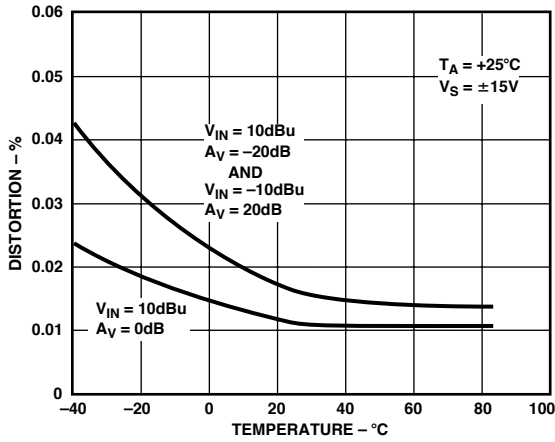
# SSM2018T



TPC 13. SSM2018T Gain vs. Frequency



TPC 16. SSM2018T Control Feedthrough Distribution



TPC 14. SSM2018T Distortion vs. Temperature

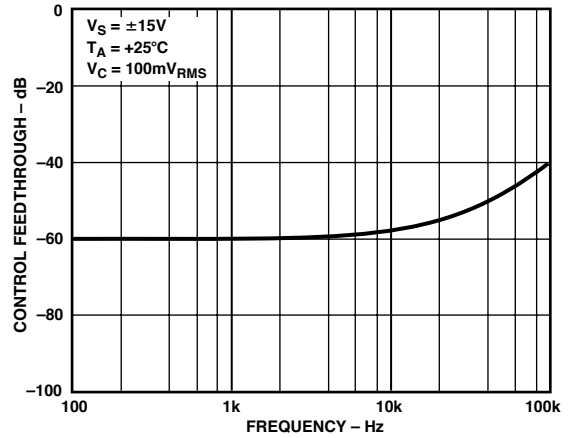
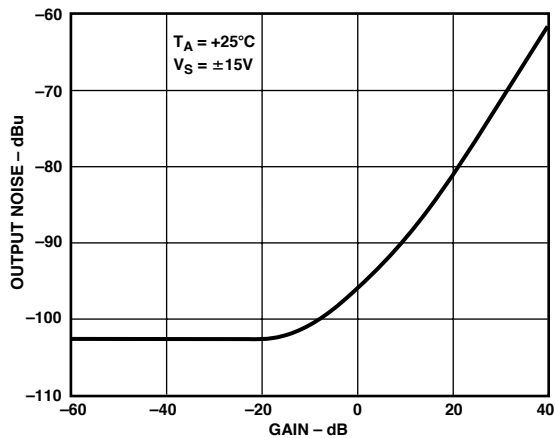
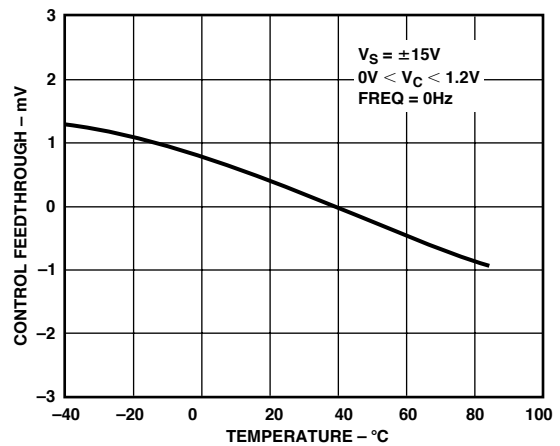


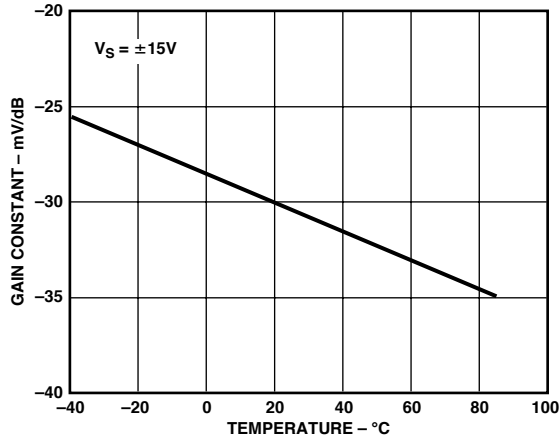
Figure 17. SSM2018T Control Feedthrough vs. Frequency



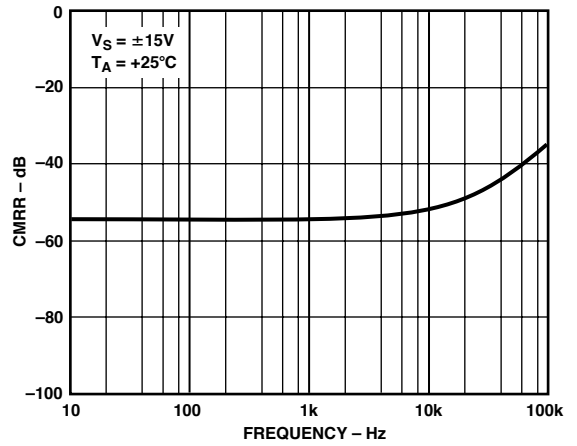
TPC 15. SSM2018T Output Noise vs. Gain ( $V_{IN} = GND$ , 20 kHz Bandwidth)



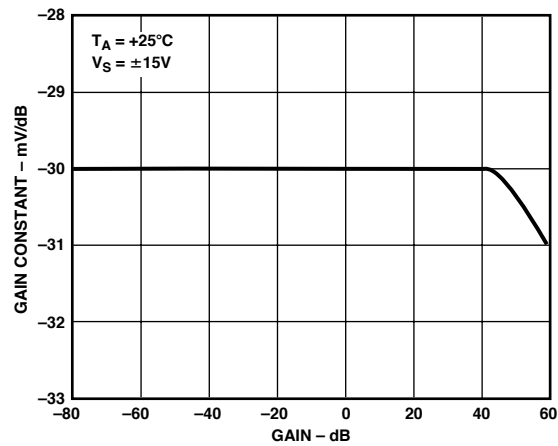
TPC 18. SSM2018T Control Feedthrough vs. Temperature



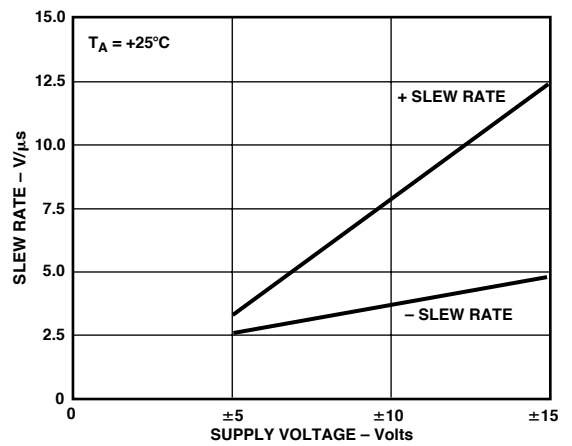
TPC 19. SSM2018T Gain Constant vs. Temperature



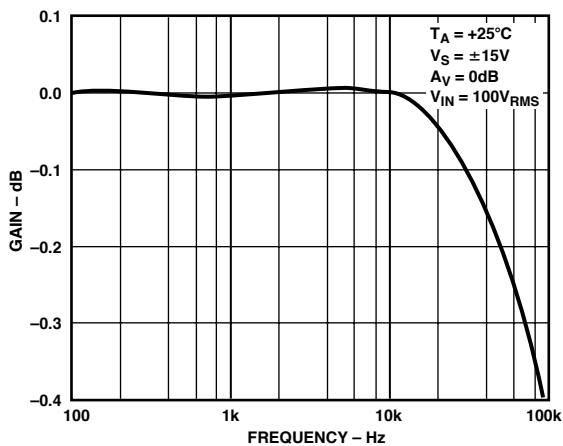
TPC 22. SSM2018T CMRR vs. Frequency



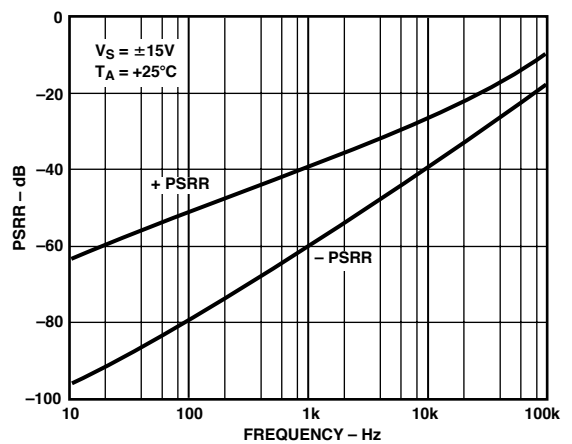
TPC 20. SSM2018T Gain Constant Linearity vs. Gain



TPC 23. SSM2018T Slew Rate vs. Supply Voltage



TPC 21. SSM2018T Gain Flatness vs. Frequency



TPC 24. SSM2018T PSRR vs. Frequency





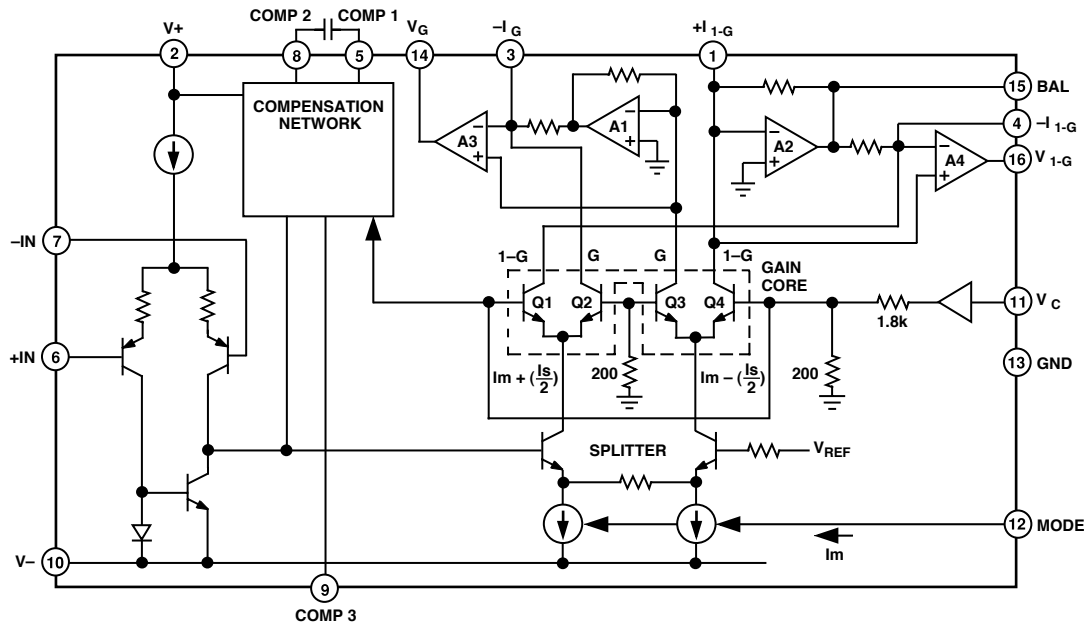


Figure 2. SSM2018T Detailed Functional Diagram

shown later in the data sheet. Thus, for the Basic VCA circuit or the OVCE circuit, COMP3 should be left open.

A compensation capacitor does need to be added between COMP1 and COMP2. Because the VCA operates over such a wide gain range, the compensation should ideally be optimized for each gain. When the VCA is in high attenuation, there is very high “loop gain,” and the part needs to have high compensation. On the other hand, at high gain, the same compensation capacitor would overcompensate the part and roll off the high frequency performance. Thus, the SSM2018T employs a patented adaptive compensation circuit. The compensation capacitor is “Miller” connected between the base and collector of an internal transistor. By changing the gain of this transistor via the control voltage, the compensation is changed.

Increasing the compensation capacitor causes the frequency response and slew rate to decrease, which tends to cause high frequency distortion to increase. For the basic VCA circuit, 47 pF was chosen as the optimal value. The OVCE circuit described later uses a 220 pF capacitor. The reason for the increase is to compensate for the extra phase shift from the additional output amplifier used in the OVCE configuration. The compensation capacitor can be adjusted over a practical range from 47 pF to 220 pF if desired. Below 47 pF, the parts may oscillate; above 220 pF the frequency response is significantly degraded.

#### Control Section

As noted above, the control voltage on Pin 11 steers the current through the gain core transistors to set the gain. The unity gain (0 dB) condition occurs at  $V_C = 0$ . Attenuation occurs in the VCA for positive voltages (0 V to 3 V, typ), and gain occurs for negative voltage (0 V to -1.3 V, typ). From -1.3 V to +3.0 V, 140 dB of gain range is obtainable. The output gain formula is as follows:

$$V_{OUT} = V_{IN} \times e^{(-aV_C)} \quad (1)$$

The exponential term arises from the standard Ebers-Moll equation describing the relationship of a transistor’s collector current as a function of the base-emitter voltage:

$$I_C = I_S \times e^{(V_{BE}/V_T)} \quad (2)$$

The factor “ $a$ ” is a function not only of  $V_T$  but also the scaling due to the resistor divider of the 200  $\Omega$  and 1.8 k $\Omega$  resistors shown in Figure 2. The resulting expression for “ $a$ ” is as follows:  $a = 1/(10 \times V_T)$ , which is approximately equal to 4 at room temperature. Substituting  $a = 4$  in the above equation results in a -28.8 mV/dB control law at room temperature.

The -28.8 mV/dB number is slightly different from the data sheet specification of -30 mV/dB. The difference arises from the temperature dependency of the control law. The term  $V_T$  is known as the thermal voltage, and it has a direct dependency on temperature:  $V_T = kT/q$  ( $k =$  Boltzmann’s constant =  $1.38E-23$ ,  $q =$  electron charge =  $1.6E-19$ , and  $T =$  absolute temperature in Kelvin). This temperature dependency leads to the -3500 ppm/ $^{\circ}C$  drift of the control law. It also means that the control law changes as the part warms up. Thus, our specification for the control law states that the part has been powered up for 60 seconds.

When the part is initially turned on, the temperature of the die is still at the ambient temperature (25 $^{\circ}C$  for example), but the power dissipation causes the die to warm up. With  $\pm 15$  V supplies and a supply current of 11 mA, 330 mW is dissipated. This number is multiplied by  $\theta_{JA}$  to determine the rise in the die’s temperature. In this case, the die increases from 25 $^{\circ}C$  to approximately 50 $^{\circ}C$ . A 25 $^{\circ}C$  temperature change causes a 8.25% increase in the gain constant, resulting in a gain constant of 30 mV/dB. The graph in Figure 17 shows how the gain constant varies over the full temperature range.

# SSM2018T

## Proper Operating Mode for the SSM2018T

The SSM2018T has the flexibility of operating in either Class A or Class AB. This is accomplished by adjusting the amount of current flowing in the gain core ( $I_M$  in Figure 2). The traditional trade-off between the two classes is that Class A tends to have lower THD but higher noise than Class AB. However, by using well matched gain core transistors, distortion compensation circuitry and laser trimming, the SSM2018T has excellent THD performance in Class AB. Thus, it offers the best of both worlds in having the low noise of Class AB with low THD.

Because the SSM2018T operates optimally in Class AB, the distortion trim is performed for this class. *To guarantee conformance to the data sheet THD specifications, the SSM2018T must be operated in class AB.* This does not mean that it can not be operated in Class A, but the optimal THD trim point is different for the two classes. Using Class A operation results to 0.05% without trim. An external potentiometer could be added to change the trim back to its optimal point as shown in the OVCE application circuit, but this adds the expense and time in adjusting a potentiometer.

The class of operation is set by selecting the proper value for  $R_B$  shown in Figure 1.  $R_B$  determines the current flowing into the MODE input (Pin 12). For class AB operation with  $\pm 15$  V supplies,  $R_B$  should be 150 k $\Omega$ . This results in a current of 95  $\mu$ A. For other supply voltages, adjust the value of  $R_B$  such that current remains at 95  $\mu$ A. This current follows the formula:

$$I_{MODE} = \frac{(V_{CC} - 0.7V)}{R_B} \quad (3)$$

The factor of 0.7 V arises from the fact that the dc bias on Pin 12 is a diode drop above ground.

## Output Drive

The SSM2018T is buffered by an internal op amp to provide a low impedance output. This output is capable of driving to within 1.2 V of either rail at 1% distortion for a 100 k $\Omega$  load. Note: This 100 k $\Omega$  load is in parallel with the feedback resistor of 18 k $\Omega$ , so the effective load is 15.3 k $\Omega$ . For better than 0.01% distortion, the output should remain about 3.5 V away from either rail as shown in TPC 2. As the graph of output swing versus load resistance shows (TPC 9), to maintain less than 1% distortion the output current should be limited to approximately  $\pm 1.3$  mA. If higher current drive is required, the output should be buffered with a high quality op amp such as the OP176 or AD797.

The internal amplifiers are compensated for unity gain stability and are capable of driving a capacitive load up to 4700 pF. Larger capacitive loads should be isolated from the output of the SSM2018T by the use of a 50  $\Omega$  series resistor.

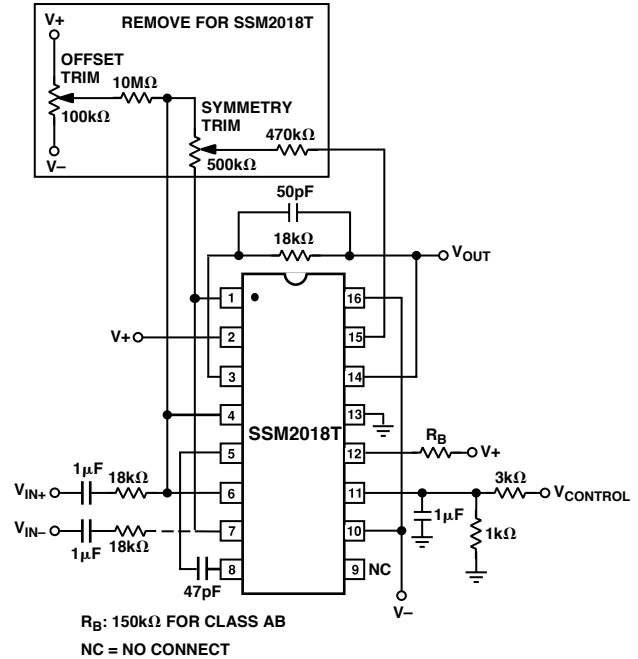


Figure 3. Upgrading SSM2018 Sockets

## Upgrading SSM2018 Sockets

The SSM2018T easily replaces the SSM2018 in the basic VCA configuration. The parts are pin for pin compatible allowing direct replacement. At the same time, the trimming potentiometers for symmetry and offset should be removed, as shown in Figure 3. Upgrading immediately to the SSM2018T saves the expense of the potentiometers and the time in production of trimming for minimum distortion and control feedthrough.

If the SSM2018 is used in the OVCE or VCP configuration, the SSM2018T can still directly replace it; however, the potentiometers cannot necessarily be removed, as explained in the OVCE and VCP sections.

## Temperature Compensation of the Gain Constant

As explained above, the gain constant has a  $-3500$  ppm/ $^{\circ}$ C temperature drift due to the inherent nature of the control port. Over the full temperature range of  $-40^{\circ}$ C to  $+85^{\circ}$ C, the drift causes the gain to change by 7 dB if the part is in a gain of  $\pm 20$  dB. If the application requires the gain constant to be the same over a wide temperature range, external temperature compensation should be employed. The simplest form of compensation is a temperature compensating resistor (TCR) such as the PT146 from Precision Resistor Co. These elements are different than a standard thermistor in that they are linear over temperature to better match the linear drift of the gain constant.

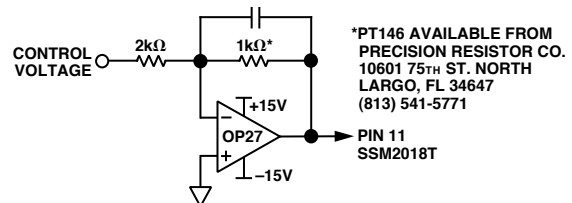


Figure 4. Two TCRs Compensate for Temperature Drift of Gain Constant



# SSM2018T

If a symmetry trim is to be performed, it should precede the control feedthrough trim and be done as follows:

1. Apply a 1 kHz sine wave of 10 dBu to the input with the control voltage set for unity gain.
2. Adjust the symmetry trim potentiometer to minimize distortion of the output signal.

Next the control feedthrough trim is done as follows:

1. Ground the input signal port and apply a 60 Hz sine wave to the control port. The sine wave should have its high and low peaks correspond to the highest gain to be used in the application and 30 dB of attenuation, respectively. For example, a range of 20 dB gain to 30 dB attenuation requires that the sine wave amplitude ranges between -560 mV and +840 mV on Pin 11.
2. Adjust the control feedthrough potentiometer to null the signal seen at the output.

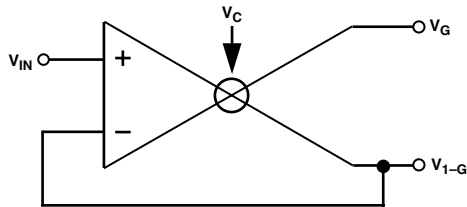


Figure 7. OVCE Follower/VCA Connection

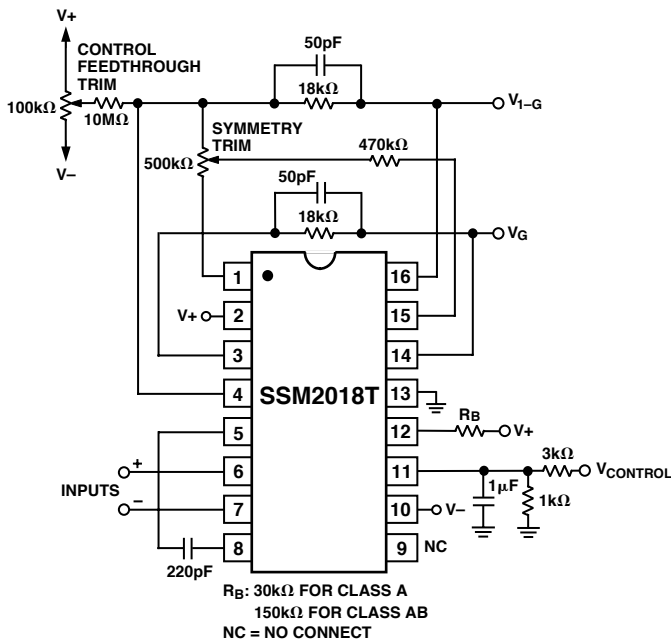


Figure 8. OVCE Application Circuit

## Voltage Controlled Panner

An interesting circuit that is built with the OVCE building block is a voltage controlled panner. Figure 9 shows the feedback connection for the circuit. Notice that the average of both outputs is fed back to the input. Thus, the average must be equal to the input voltage. When the control voltage is set for gain at  $V_G$ , this causes  $V_{1-G}$  to attenuate (to keep the average the same). On the other hand, when  $V_G$  is attenuated,  $V_{1-G}$  is amplified. The result is that the control voltage causes the input to “pan” from one output to the other. The following expressions show how this circuit works mathematically:

$$V_G = 2K \times V_{IN} \text{ and } V_{1-G} = 2(1-K) \times V_{IN} \quad (4)$$

where  $K$  varies between 0 and 1 as the control voltage is changed from full attenuation to full gain, respectively. When  $V_C = 0$ , then  $K = 0.5$  and  $V_G = V_{1-G} = V_{IN}$ . Again, trimming is required for best performance. Pin 9 must be grounded. This is possible because the feedback is constant and the adaptive network is not needed. The VCP is the only application shown in this data sheet where Pin 9 is grounded.

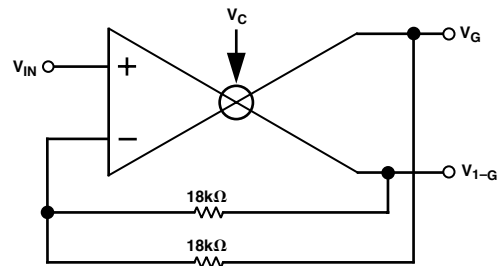
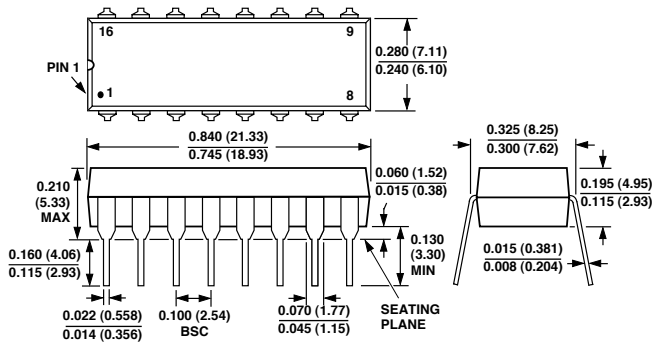


Figure 9. Basic VCP Connection

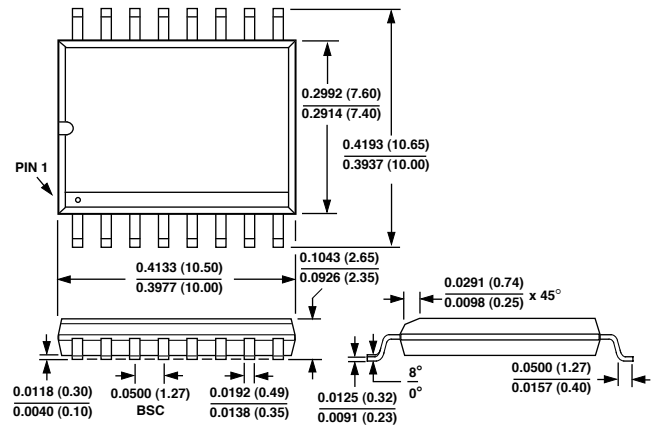
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

16-Lead Plastic DIP (N-16) Package



16-Lead SOIC (R-16) Package



Revision History

Location

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7/02—Data Sheet changed from REV. A to REV. B.

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